



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventors: Hamza Yilmaz
Assignee:
Title: Semiconductor Device Containing Dielectrically Isolated PN Junction
For Enhanced Breakdown Characteristics
Serial No.: 10/771,593 Filing Date: 02/02/2004
Examiner: Fetsum Abraham Group Art Unit: 2826
Docket No.: YMZ004 US Confirmation No: 3820

Santa Clara, California
August 16, 2005

COMMISSIONER FOR PATENTS
P.O. BOX 1450
ALEXANDRIA, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, §1.97 and §1.98, Applicant submits for consideration in the above-identified patent application the documents listed on the accompanying Form PTO-1449. The Examiner is requested to make these documents of record.

This Information Disclosure Statement is submitted in conjunction with the accompanying Request for Continued Examination.

Applicant would appreciate the Examiner initialing and returning the Form PTO-1449, indicating that the information has been considered and made of record herein.

Applicant states that each item of information contained in the information disclosure statement was first cited in an International Search Report prepared by the European Patent Office in a counterpart PCT application not more than three months prior to the filing of the information disclosure statement. A copy of the International Search Report is also enclosed.

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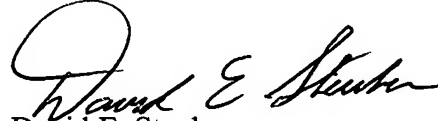
The information contained in this Information Disclosure Statement is to the best of my knowledge and is not to be construed as a representation that: (i) a complete search has been made; (ii) additional information material to the examination of this application does not exist; (iii) the information, protocols, results and the like reported by third parties are accurate or enabling; or (iv) the above information constitutes prior art to the subject invention.

CERTIFICATE OF MAILING BY "FIRST CLASS"

I hereby certify that this paper or fee is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. BOX 1450, Alexandria, VA. 22313-1450 on the above date.


David E. Steuber

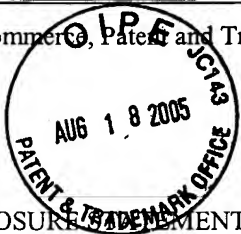
Respectfully submitted,



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U.S. Department of Commerce, Patent and Trademark Office  INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Application No.:	10/771,593
	Filing Date:	02/02/2004
	First Named Inventor:	Hamza Yilmaz
	Group Art Unit:	2826
	Examiner Name:	Fetsum Abraham
	Confirmation No.:	3820
	Attorney Docket No.:	YMZ004 US

U.S. Patent Documents

*Examiner Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1.	2004/0084721 A1	05/06/2004	Kocon et al.	257	328	11/05/2002

Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	2.	EP 1073110 A1	01/31/2001	Europe	21	329		X
	3.	EP 1369927 A2	12/10/2003	Europe	29	78		
	4.	JP 07142713	06/02/1995	Japan	29	78		X
	5.	JP 08102538	04/16/1996	Japan	29	78		X

Non Patent Literature Documents

	6.	Gupta, R.N. et al., A Novel Planarized, Silicon Trench Sidewall Oxide-Merged p-i-n Schottky (TSOX-MPS) Rectifier, IEEE Electron Device Letters, Vol. 20, No. 12, December 1999
	7.	Chang, H.R. et al., Development and Demonstration of Silicon Carbide (SiC) Motor Drive Inverter Modules, 2003 IEEE 34 th Annual Power Electronics Specialists Conference (PESC) Conference Proceedings, Acapulco, Mexico, 06/15/2003

Examiner:	Date Considered:
* Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication with applicant.	